

100A BIDIRECTIONAL SURFACE MOUNT THYRISTOR SURGE PROTECTIVE DEVICE

Features

- 100A Peak Pulse Current @ 10/1000µs
- 400A Peak Pulse Current @ 8/20µs
- 58 - 320V Stand-Off Voltages
- Oxide-Glass Passivated Junction
- Bidirectional Protection In a Single Device
- High Off-State Impedance and Low On-State Voltage
- Helps Equipment Meet GR-1089-CORE, IEC 61000-4-5, FCC Part 68, ITU-T K.20/K.21, and UL497B
- UL Listed Under Recognized Component Index, File Number 156346
- **Lead Free Finish/RoHS Compliant (Note 1)**
- **Green Molding Compound (No Halogen and Antimony) (Note 2)**

Mechanical Data

- Case: SMB
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Lead Free Plating (Matte Tin Finish). Solderable per MIL-STD-202, Method 208
- Polarity: None; Bidirectional Devices Have No Polarity Indicator
- Weight: 0.093 grams (approximate)



Top View



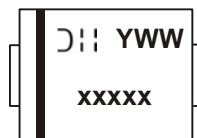
Bottom View

Ordering Information (Note 3)

Part Number	Case	Packaging
TB0640H-13-F	SMB	3000/Tape & Reel
TB0720H-13-F	SMB	3000/Tape & Reel
TB0900H-13-F	SMB	3000/Tape & Reel
TB1100H-13-F	SMB	3000/Tape & Reel
TB1300H-13-F	SMB	3000/Tape & Reel
TB1500H-13-F	SMB	3000/Tape & Reel
TB1800H-13-F	SMB	3000/Tape & Reel
TB2300H-13-F	SMB	3000/Tape & Reel
TB2600H-13-F	SMB	3000/Tape & Reel
TB3100H-13-F	SMB	3000/Tape & Reel
TB3500H-13-F	SMB	3000/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied, see EU Directive 2002/95/EC Annex Notes.
 2. Product manufactured with Data Code 0924 (week 24, 2009) and newer are built with Green Molding Compound.
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



xxxxx = Product type marking code (See table on page 2)
 DII = Manufacturers' code marking
 YWW = Date code marking
 Y = Last digit of year (ex: 6 for 2006)
 WW = Week code (01 to 53)

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.
 For capacitance load, derate current by 20%.

Characteristic	Symbol	Value	Unit
Non-Repetitive Peak Impulse Current @10/1000us	I_{pp}	100	A
Non-Repetitive Peak On-State Current @8.3ms (one-half cycle)	I_{TSM}	50	A
Typical Positive Temperature Coefficient for Breakdown Voltage	$\Delta V_{BR}/\Delta T_J$	0.1	%/ $^\circ\text{C}$

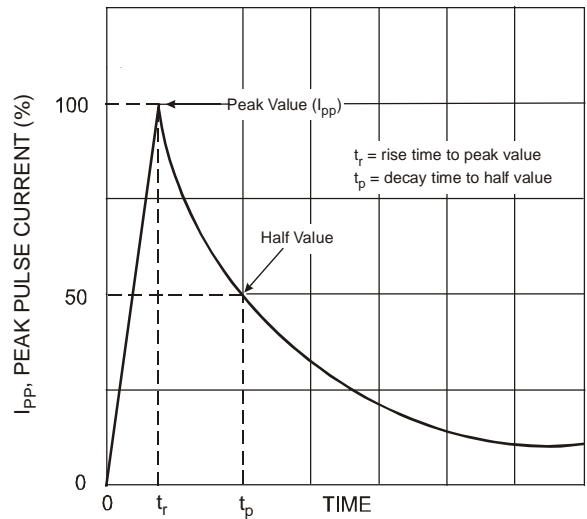
Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	20	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	100	$^\circ\text{C}/\text{W}$
Junction Temperature Range	T_J	-40 to +150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ\text{C}$

Maximum Rated Surge Waveform

Waveform	Standard	I_{pp} (A)
2/10 μs	GR-1089-CORE	500
8/20 μs	IEC 61000-4-5	400
10/160 μs	FCC Part 68	250
10/700 μs (Note 4)	ITU-T, K.20/K.21	200
10/560 μs	FCC Part 68	160
10/1000 μs	GR-1089-CORE	100

Notes: 4. Applied 6kV, 10/700 μs waveform



Electrical Characteristics @T_A = 25°C unless otherwise specified

Part Number	Maximum Rated Repetitive Off-State Voltage	Maximum Off-State Leakage Current @ V _{DRM}	Maximum Breakover Voltage	Maximum On-State Voltage @ I _T = 1A	Breakover Current I _{BO}		Holding Current I _H		Typical Off-State Capacitance	Marking Code
	V _{DRM} (V)	I _{DRM} (µA)	V _{BO} (V)	V _T (V)	Min (mA)	Max (mA)	Min (mA)	Max (mA)	C _O (pF)	
TB0640H	58	5	77	3.5	50	800	150	800	200	T064H
TB0720H	65	5	88	3.5	50	800	150	800	200	T072H
TB0900H	75	5	98	3.5	50	800	150	800	200	T090H
TB1100H	90	5	130	3.5	50	800	150	800	120	T110H
TB1300H	120	5	160	3.5	50	800	150	800	120	T130H
TB1500H	140	5	180	3.5	50	800	150	800	120	T150H
TB1800H	160	5	220	3.5	50	800	150	800	120	T180H
TB2300H	190	5	265	3.5	50	800	150	800	80	T230H
TB2600H	220	5	300	3.5	50	800	150	800	80	T260H
TB3100H	275	5	350	3.5	50	800	150	800	80	T310H
TB3500H	320	5	400	3.5	50	800	150	800	80	T350H

Symbol	Parameter
V _{DRM}	Stand-off Voltage
I _{DRM}	Leakage current at stand-off voltage
V _{BR}	Breakdown voltage
I _{BR}	Breakdown current
V _{BO}	Breakover voltage
I _{BO}	Breakover current
I _H	Holding current (Note 5)
V _T	On state voltage
I _{PP}	Peak pulse current
C _O	Off-state capacitance (Note 6)

- Notes:
- I_H > (V_L/R_L) If this criterion is not obeyed, the TSPD triggers but does not return correctly to high-resistance state. The surge recovery time does not exceed 30ms.
 - Off-state capacitance measured at f = 1.0MHz, 1.0V_{RMS} signal, V_R = 2V_{DC} bias.





Fig. 1 Off-State Current vs. Junction Temperature



Fig. 2 Relative Variation of Breakdown Voltage vs. Junction Temperature



Fig. 3 Relative Variation of Breakover Voltage vs. Junction Temperature



Fig. 4 On-State Current vs. On-State Voltage



Fig. 5 Relative Variation of Holding Current vs. Junction Temperature



Fig. 6 Relative Variation of Junction Capacitance vs. Reverse Voltage Bias

Package Outline Dimensions



SMB		
Dim	Min	Max
A	3.30	3.94
B	4.06	4.57
C	1.96	2.21
D	0.15	0.31
E	5.00	5.59
G	0.05	0.20
H	0.76	1.52
J	2.00	2.50

All Dimensions in mm

Suggested Pad Layout



Dimensions	Value (in mm)
Z	6.8
G	1.8
X	2.3
Y	2.5
C	4.3

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